

ABSTRACT

A plasma processing system has a susceptor, provided in a processing vessel, for supporting thereon a substrate.

5 A process gas is supplied into the processing vessel to produce the plasma of the process gas. The susceptor has a dielectric film formed on a base, and a plurality of protrusions formed on the film. The protrusions of the susceptor are formed by thermal-spraying a ceramic onto the dielectric film via an aperture plate having a plurality of circular apertures.